

UNITED STATES PATENT APPLICATION

of

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for

**A METHOD FOR FORMING A SEMICONDUCTOR DEVICE, AND A
SEMICONDUCTOR DEVICE FORMED BY THE METHOD**

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5 The present invention relates to a semiconductor device, and a method for forming the semiconductor device. In particular, the invention relates to a method for forming a multi-layer semiconductor device in which at least two of the layers are bonded by an annealing bonding process.

As miniaturisation requirements in the semiconductor industry grow, the demand for semiconductor devices with increasing numbers of features similarly grows. In the field of laser and sensor technology semiconductor devices which include micro-electro-mechanical components and micro-opto-electro-mechanical components are commonly required. Such devices are typically multi-layer devices which include multiple layers of semiconductor material and/or other suitable materials. The micro-components are typically formed in one of the semiconductor layers, while circuitry is formed in the other layers, and may also be formed on the micro-component layer. The circuitry may be provided for controlling the micro-components and may also be provided for other functions. In certain cases some or all of the circuitry for controlling the micro-components may be provided on a separate discrete semiconductor device. In general, it is desirable, and indeed in many cases it is a requirement that the respective semiconductor layers should be electrically insulated, one from the other. This requires the formation of insulating layers between the respective semiconductor layers. Such insulating layers, are typically provided by oxide layers, which may be grown or deposited. Because of the number of semiconductor layers, in general, it is necessary to bond some of the layers together by suitable bonding processes, typically, high temperature annealing processes. Typically, a semiconductor layer is bonded to an oxide layer which had been grown or deposited on another semiconductor layer. The surface of the semiconductor layer to be bonded to the oxide layer, in general, is ground and polished to a high degree of smoothness for providing a smooth surface for abutting the oxide layer on the other semiconductor layer. The oxide layer, in general,

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Summary of the Invention

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prior to bonding the one of the second and third layers to the second etch stop layer, patterning the second etch stop layer to define the component in the second layer for facilitating etching of the second layer through the third layer,

- etching the second layer through the third layer and the second etch stop layer for forming the component in the second layer.

13 Advantageously, the portion of the third layer adjacent the component which is etched for exposing the component is etched to the second etch stop layer. Ideally, the second layer is etched to the first etch stop layer for forming the component.

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In one embodiment of the invention a communicating bore is formed through the first layer communicating with the first etch stop layer for facilitating etching of the portion of the first etch stop layer adjacent the component for forming the void between the component and the first layer. Preferably, prior to etching the second layer for forming the component initially only a part of the portion of the first etch stop layer is etched through the communicating bore in the first layer for thinning the first etch stop layer for minimising stresses induced in the portion of the second layer from which the component is to be formed.

In another embodiment of the invention the first etch stop layer is bonded to one of the first and second layers, and is bonded to the one of the first and second layers prior to the second etch stop layer being bonded to the one of the second and third layers. Preferably, the second etch stop layer is formed on the second layer after bonding of the first etch stop layer to the respective one of the first and second layers.

In one embodiment of the invention the first and second etch stop layers are grown layers.

Preferably, the second etch stop layer is grown on the second layer, and the second etch stop layer is bonded to the third layer. Advantageously, the first etch stop layer is grown on the first layer, and the first etch stop layer is bonded to the second layer. Ideally, each of the first and second etch stop layers which are bonded to an adjacent one of first, second and third layers are bonded to the adjacent layer by annealing. Preferably, the annealing bonding step is carried out at a temperature in the range of 900°C to 1,200°C. Advantageously, the annealing bonding step is carried out at a temperature in the order of 1,000°C.

In one embodiment of the invention the first and second etch stop layers are oxide layers.

In another embodiment of the invention the second etch stop layer is patterned by depositing a photoresist layer on the second etch stop layer and exposing and developing a pattern which defines the component on the photoresist layer, and subsequently etching the second etch stop layer to define the component.

In another embodiment of the invention the first, second and third layers are of semiconductor material.

In one embodiment of the invention the first, second and third layers are of silicon material.

5 In one embodiment of the invention the component is a micro-mechanical component.

10. In a further embodiment of the invention the component is a micro-optical component.

In one embodiment of the invention the depth of the first etch stop layer is at least twice the depth of the second etch stop layer.

30 prior to forming the component in the second layer forming a communicating bore through the first layer communicating with the first etch stop layer adjacent a portion of the second layer where the component is to be formed, and etching a part of a portion of the first etch stop layer adjacent the portion of the second layer where the component is to be formed for thinning the first etch stop layer adjacent the portion of the second layer where the component is to be formed to an effective stress relieving depth for relieving stress in the portion of the second

layer where the component is to be formed.

In one embodiment of the invention the portion of the first etch stop layer adjacent the component is thinned to a depth relative to the depth of the second etch stop layer for relieving stress in the portion of the second layer where the component is to be formed.

In another embodiment of the invention the portion of the first etch stop layer adjacent the component is thinned to a depth so that the difference in thicknesses of the respective first and second etch stop layers does not exceed 2 microns. Preferably, the portion of the first etch stop layer adjacent the component is thinned to a depth so that the difference in thicknesses of the respective first and second etch stop layers does not exceed 1 micron.

In another embodiment of the invention the depth of the first etch stop layer is at least twice the depth of the second etch stop layer.

Preferably, the first etch stop layer is bonded to one of the first and second layers.

In one embodiment of the invention the first etch stop layer is a grown layer.

In one embodiment of the invention the area in plan view of the portion of the first etch stop layer which is thinned is less than the area in plan view of the component.

Preferably, the area in plan view of the portion of the first etch stop layer which is thinned is at least half the area in plan view of the component.

Advantageously, the area in plan view of the portion of the first etch stop layer which is thinned is at least three-quarters the area in plan view of the component.

In one embodiment of the invention the cross-sectional area of the communicating bore through the first layer is at least half the area of the component in plan view.

Further the invention provides a semiconductor device comprising:

first, second and third layers.

a component formed in the second layer, and

• first and second etch stop layers located between the first and second layers, and the second and third layers, respectively, at least the second etch stop layer being bonded to one of the second and third layers, wherein

10 prior to bonding the second etch stop layer to the one of the second and third layers, the second etch stop layer is patterned to define the component in the second layer for facilitating etching of the second layer through the third layer and the second etch stop layer, and the second layer is etched subsequent to the second etch stop layer having been bonded to the one of the first and second layers.

15 In one embodiment of the invention a portion of the third layer adjacent the component is etched for forming an opening through the third layer exposing the component.

20 In another embodiment of the invention a portion of the second etch stop layer adjacent the component is etched for removing the second etch stop layer from the component.

25 In a further embodiment of the invention a portion of the first etch stop layer adjacent the component is etched for removing the first etch stop layer from the component and for forming a void between the component and the first layer.

Preferably, the first etch stop layer is etched through a communicating bore formed through the first layer communicating with the first etch stop layer.

30 In one embodiment of the invention the first and second etch stop layers are oxide layers.

5 In another embodiment of the invention the first, second and third layers are of silicon material.

10 In a still further embodiment of the invention the component is a micro-optical component.

The advantages of the invention are many. A particularly important advantage of the invention is that the method of the invention permits forming of components in the second layer which is located between first and third layers after the layers have been assembled. This would otherwise be difficult, if not impossible. If components were to be formed in the second layer after the three layers had been assembled, without using the method of the invention, it would be necessary to initially etch the first or the third layer to expose the portions of the second layer to be etched for forming the components. The exposed portions of the second layer would then have to be patterned through the first or the third layer, and subsequently etched. Patterning the second layer through a relatively deep first or third layer would be difficult if not impossible. Accordingly, by patterning the second etch stop layer prior to assembling the second and third layers permits the second layer to be readily and easily etched through the third layer and the second etch stop layer, and furthermore, and of particular importance permits accurate etching of the second layer through the third layer and the second etch stop layer. From this advantage many other important advantages follow. For example, since the first, second and third layers of the semiconductor device can be assembled and bonded or otherwise formed together prior to the formation of the component in the second layer, the formation of the component in the second layer can be left to one of the last, if not the actual last set of operations in the formation of the semiconductor device. Thus,

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Brief Description of the Drawings

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Fig. 2 is a transverse cross-sectional side elevational view of the semiconductor device of Fig. 1 on the line II-II of Fig. 1,

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Figs. 4 to 7 are front elevational views of the semiconductor device of Fig. 1 in the process of being formed, and

Figs. 8 to 11 are transverse cross-sectional front elevational views of the semiconductor device of Fig. 1 on the line II-II of Fig. 1 also being formed.

5 Detailed Description of Preferred Embodiments

Referring to the drawings there is illustrated a multi-layer semiconductor device according to the invention indicated generally by the reference numeral 1. In this embodiment of the invention the semiconductor device 1 comprises three semiconductor layers, namely, a first layer, which is a lower layer 4, a second layer, namely, an intermediate layer 5, and a third layer, namely, an upper layer 6, all of which are of single crystal silicon. The layers 4, 5 and 6 are insulated from each other by respective insulating layers, which also act as etch stop layers, namely, a first etch stop layer 8 which is located between the lower and intermediate layers 4 and 5, and a second etch stop layer 9 which is located between the intermediate and upper layers 5 and 6. The first and second etch stop layers 8 and 9 are both oxide layers which in this embodiment of the invention are grown on their respective adjacent lower and intermediate layers 4 and 5, respectively. The intermediate layer 5 and the upper layer 6 are bonded to the first and second etch stop layers 8 and 9, respectively, by an annealing process as will be described below, and thus, the first and second etch stop layers 8 and 9 are also bondable layers.

Two components, in this embodiment of the invention micro-opto-electro-mechanical components, namely, circular micro-mirrors 10 are formed in the intermediate layer 5 by etching as will be described below. The micro-mirrors 10 are each connected to the intermediate layer 5 by respective pairs of connecting arms 11 which are etched from the intermediate layer 5 during the etching of the micro-mirrors 10, see Fig. 3. The connecting arms 11 are arranged at 180° intervals around the respective micro-mirrors 10, and are sized and shaped to be resilient and flexible for facilitating displacement of the micro-mirrors 10 relative to the intermediate layer 5 for facilitating directional control and/or filtering of laser light instant on the micro-mirrors 10. This aspect of micro-mirrors 10 will be well known to those skilled in the art. The surfaces of the micro-mirrors 10 which are to be made reflective are coated with an appropriate reflective material, for example, gold or the like. The reflective coating is

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Fig. 9.

Referring now to Fig. 10 a pair of communicating fusto-conical bores 30 of circular cross-section are next etched through the lower layer 4 to the first etch stop layer 8 by a deep reactive ion etch. The communicating bores 30 are centrally aligned with the corresponding micro-mirrors 10 for facilitating subsequent etching of portions of the first etch stop layer 8 adjacent the micro-mirrors 10 for forming respective voids 31, see Fig. 2, beneath the micro-mirrors 10 for facilitating displacement and/or swivelling of the micro-mirrors 10. The communicating bores 30 are formed by appropriately patterning the lower surface 22 of the lower layer 4, and then etching the lower layer 4 through the pattern.

In this embodiment of the invention as discussed above the first etch stop layer 8 is of 2 microns deep, while the second etch stop layer 9 is of 0.5 micron deep. The first etch stop layer 8 as well as acting as an etch stop layer and an insulator, also acts as a spacer for spacing the intermediate layer 5 and the lower layer 4 apart from each other so that when the voids 31 beneath the micro-mirrors 10 are formed the voids 31 are of sufficient depth for facilitating adequate displacement and/or swivelling of the micro-mirrors 10. However, since the second etch stop layer 9 does not have to act as a spacer, since the upper layer 6 fulfils that function the second etch stop layer 9 may be significantly thinner than the first etch stop layer 8, and for facilitating efficiency of manufacture of the semiconductor device 1 the second etch stop layer 9 is kept to a minimum thickness, namely, 0.5 micron. However, the provision of oxide layers, and in particular the provision of oxide layers of different depths, on respective opposite sides of a relatively thin film of silicon, as in the case of the micro-mirrors 10 formed in the intermediate layer 5 causes undesirable stresses to be induced in the relatively thin layer of silicon. Accordingly, if the micro-mirrors 10 were etched from the intermediate layer 5 with adjacent portions of the first and second etch stop layers 8 and 9 located on respective opposite sides of the micro-mirrors 10 undesirable stresses would be introduced into the micro-mirrors 10 which could lead to distortion, in particular, bowing of the micro-mirrors 10. In order to avoid this problem prior to etching the micro-mirrors 10 from the intermediate layer 5, portions of the first etch stop layer 8 adjacent the micro-mirrors 10 are thinned

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Thereafter the assembly is subjected to a wet oxide etch for etching the portions 35 of the second oxide layer 9 from the micro-mirrors 10 and the connecting arms 11,

and for etching the first etch stop layer 8 for forming the voids 31 beneath the micro-mirrors 10. The wet etch is carried out through the openings 16 in the upper layer 6 and the communicating bores 30 in the lower layer 4. At this stage the assembly is ready for receiving and securing other components to the upper layer 6 above the openings 16.

While the semiconductor device has been described as comprising only two micro-mechanical components which in these embodiments of the invention are micro-opto-electro-mechanical components any number of components may be provided, and in practice, it is envisaged that a matrix of many components may be provided in the device in the intermediate layer. The matrix of components may comprise components which are the same or different. The reason that the semiconductor device has been described as comprising only two such micro-mechanical components has been solely for the purpose of ease of illustration and description.

While the semiconductor device has been described as comprising three semiconductor layers, the semiconductor device may be provided with any number of semiconductor layers from two upwards. Indeed, it is also envisaged that all the layers need not be of semiconductor material. The layers from which the micro-mechanical components are to be formed may be of any other suitable material. It will of course be appreciated that the semiconductor layers may be of material other than single crystal silicon, for example, polysilicon and the like.

It is also envisaged that the etch stop layers may be formed by processes other than by growing the oxide layers, for example, the oxide layers of the etch stop layer may be deposited. It will also be appreciated that other suitable etch stop layers may be used besides oxide layers.

As discussed above, it will be readily apparent to those skilled in the art that multi-layer semiconductor devices with layers of depth other than those already described may be provided.

It will be appreciated that while the micro-mechanical components have been

described as being micro-mirrors, any other micro-mechanical components may be formed in the intermediate layer. For example, any other type of membrane component may be formed in the intermediate layer, such as pressure sensors, other light controlling devices, for example, filters, devices for attenuating light, directing and redirecting light.

It will also of course be appreciated that while the micro-mirrors have been described as being of circular shape, the micro-mirrors may be of any other suitable or desired shape, for example, square, rectangular, triangular, hexagonal, octagonal, or indeed any other polygonal shape. Needless to say, where other components besides micro-mirrors are formed in the intermediate layer, the components may likewise be of any other desired or suitable shape.

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